

L Number	Hits	Search Text	DB	Time stamp
1	0	174/141.ccls.	USPAT	2004/04/26 14:27
2	10	174/141c.ccls.	USPAT	2004/04/26 14:28
3	222	174/149r.ccls.	USPAT	2004/04/26 14:28
4	232	174/141c.ccls. 174/149r.ccls.	USPAT	2004/04/26 14:28
5	0	(174/141c.ccls. 174/149r.ccls.) and ("low k" "low-k")	USPAT	2004/04/26 14:29
6	2	(174/141c.ccls. 174/149r.ccls.) and carbon	USPAT	2004/04/26 14:29
7	0	(174/141c.ccls. 174/149r.ccls.) and "silicon oxide"	USPAT	2004/04/26 14:29
-	3908	"integrated circuit" and photodiode	USPAT; EPO; JPO	2003/01/14 13:29
-	9061	photo adj diode	USPAT; EPO; JPO	2003/01/13 15:28
-	1030	"integrated circuit" and (photo adj diode)	USPAT; EPO; JPO	2003/01/13 15:29
-	4304	("integrated circuit" and (photo adj diode)) or ("integrated circuit" and photodiode)	USPAT	2003/01/13 15:29
-	338	((("integrated circuit" and (photo adj diode)) or ("integrated circuit" and photodiode)) and "p-n"	USPAT	2003/01/13 15:30
-	164	((("integrated circuit" and (photo adj diode)) or ("integrated circuit" and photodiode)) and "p-n") and (capacitor capacitive)	USPAT	2003/01/13 15:43
-	0	"integrated circuit" and 5307169.pn.	USPAT; EPO; JPO	2003/01/13 15:45
-	1	5307169.pn.	USPAT; EPO; JPO	2003/01/13 15:45
-	0	5307169.pn. and "integrated circuit"	USPAT; EPO; JPO	2003/01/13 15:45
-	1	6207587.pn.	USPAT	2003/01/20 17:51
-	3053	information adj processing adj system	USPAT	2003/01/20 17:51
-	422	(information adj processing adj system) and "integrated circuit"	USPAT	2003/01/20 17:52
-	35	((information adj processing adj system) and "integrated circuit") and ("photo gate" "photo diode" photodiode)	USPAT	2003/01/20 17:52
-	1962	"low k"	USPAT; EPO; JPO	2003/01/23 15:49
-	244	"low k" and void	USPAT; EPO; JPO	2003/01/23 16:01
-	1310	"low k" and oxide	USPAT; EPO; JPO	2003/01/23 16:02
-	1222	("low k" and oxide) and (metal conductive lines)	USPAT; EPO; JPO	2003/01/23 16:02
-	1021	((("low k" and oxide) and (metal conductive lines)) not ("low k" and void)	USPAT; EPO; JPO	2003/01/23 16:18
-	30	breadloaf and semiconductor	USPAT; EPO; JPO	2003/01/23 17:11
-	4	("5708303" "5818111" "5821621" "5302233").pn.	USPAT; EPO; JPO	2003/01/23 17:21
-	0	((("5708303" "5818111" "5821621" "5302233").pn.) and carbon	USPAT	2003/01/23 17:14
-	28	hsq near carbon	USPAT	2003/01/23 17:14
-	0	"5821621".pn. and void	USPAT; EPO; JPO	2003/01/23 17:21
-	1	5821621.pn.	USPAT	2003/06/17 17:01
-	1	5821621.pn. and "20"	USPAT	2003/06/17 17:01
-	1	5281621.pn.	USPAT	2004/03/23 13:00
-	0	5281621.	USPAT	2004/03/23 13:00
-	1	5281621.pn.	USPAT	2004/03/23 13:01
-	1	5821621.pn.	USPAT	2004/03/23 13:01
-	718	438/787.ccls. 438/789.ccls.	USPAT	2004/03/29 15:16
-	2381830	void adj3 free) (voidless) (without with3 void\$	USPAT	2004/03/29 15:17
-	620	(void adj3 free) (voidless) (without with3 void\$) and (438/787.ccls. 438/789.ccls.)	USPAT	2004/03/29 15:18
-	17896	low adj2 k) (low adj2 dielectric	USPAT	2004/03/29 15:18

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-	17896	low adj2 k) (low adj2 dielectric) ("low-k dielectric") ("low k dielectric"	USPAT	2004/03/29 15:19
-	193	((void adj3 free) (voidless) (without with3 void\$) and (438/787.ccls. 438/789.ccls.)) and (low adj2 k) (low adj2 dielectric) ("low-k dielectric") ("low k dielectric")	USPAT	2004/03/29 15:29
-	121	((void adj3 free) (voidless) (without with3 void\$) and (438/787.ccls. 438/789.ccls.)) and (low adj2 k) (low adj2 dielectric) ("low-k dielectric") ("low k dielectric")) and (cmp planariz\$5)	USPAT	2004/03/29 15:29
-	422	438/789.ccls. 438/790.ccls.	USPAT	2004/04/16 11:25
-	10424	"void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1)	USPAT	2004/04/16 11:26
-	57	("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1)) and (438/789.ccls. 438/790.ccls.)	USPAT	2004/04/16 11:27
-	2738	"low k" "low-k" "low k dielectric"	USPAT	2004/04/16 11:27
-	46582	(carbon near2 doped) with5 "silicon oxide"	USPAT	2004/04/16 11:29
-	915	((carbon near2 doped) with5 "silicon oxide") and ("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1))	USPAT	2004/04/16 11:28
-	1043	((carbon near2 doped) with5 "silicon oxide") and ("low k" "low-k" "low k dielectric")	USPAT	2004/04/16 11:28
-	38	((carbon near2 doped) with5 "silicon oxide") and (("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1)) and (438/789.ccls. 438/790.ccls.))	USPAT	2004/04/16 11:28
-	369	"carbon-doped silicon" (carbon near2 dop\$3 near2 (silicon oxide))	USPAT	2004/04/16 11:30
-	21	("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1)) and ("carbon-doped silicon" (carbon near2 dop\$3 near2 (silicon oxide)))	USPAT	2004/04/16 11:41
-	1952	438/624.ccls. 438/763.ccls. 438/631.ccls.	USPAT	2004/04/16 11:41
-	268	"black diamond"	USPAT	2004/04/16 11:42
-	10	"black diamond" and ("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1))	USPAT	2004/04/16 11:42
-	658	252/1.ccls.	USPAT	2004/04/16 11:43
-	2933	(438/789.ccls. 438/790.ccls.) 252/1.ccls. (438/624.ccls. 438/763.ccls. 438/631.ccls.)	USPAT	2004/04/16 11:43
-	1124	((438/789.ccls. 438/790.ccls.) 252/1.ccls. (438/624.ccls. 438/763.ccls. 438/631.ccls.)) and ((carbon near2 doped) with5 "silicon oxide")	USPAT	2004/04/16 11:43
-	47	((438/789.ccls. 438/790.ccls.) 252/1.ccls. (438/624.ccls. 438/763.ccls. 438/631.ccls.)) and ((carbon near2 doped) with5 "silicon oxide")) and ("carbon-doped silicon" (carbon near2 dop\$3 near2 (silicon oxide)))	USPAT	2004/04/16 12:19
-	775	(carbonaceous adj2 (silicon oxide)) SiOC	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:19
-	221	trikon	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:22
-	152	trikon and (speed deposition rate)	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:22
-	80	trikon and (speed "deposition rate")	USPAT; US-PGPUB; EPO; JPO	2004/04/16 13:12
-	3	((carbonaceous adj2 (silicon oxide)) SiOC) and (trikon and (speed "deposition rate"))	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:24
-	36	((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon doped" "carbon-doped")	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:24

-	39	(((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon doped" "carbon-doped")) (((carbonaceous adj2 (silicon oxide)) SiOC) and (trikon and (speed "deposition rate"))))	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:27
-	4	(((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon doped" "carbon-doped")) (((carbonaceous adj2 (silicon oxide)) SiOC) and (trikon and (speed "deposition rate")))) and trikon	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:25
-	6	(((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon doped" "carbon-doped")) (((carbonaceous adj2 (silicon oxide)) SiOC) and (trikon and (speed "deposition rate")))) and ("deposition rate")	USPAT; US-PGPUB; EPO; JPO	2004/04/16 12:27
-	520521	"Pursuing the Perfect Low-k Dielectric"	USPAT; DERWENT; IBM_TDB	2004/04/16 13:09
-	308324	"Pursuing the Perfect Low-k Dielectric".ti.	USPAT; DERWENT; IBM_TDB	2004/04/16 13:10
-	73421	"Pursuing the Perfect Low-k Dielectric".ti.	DERWENT; IBM_TDB	2004/04/16 13:10
-	0	"pursuing the perfect low-k dielectric"	DERWENT; IBM_TDB	2004/04/16 13:11
-	0	"pursuing the perfect low-k dielectric"	USPAT; DERWENT; IBM_TDB	2004/04/16 13:11
-	43	trikon and (speed "deposition rate") and peters	USPAT; US-PGPUB; EPO; JPO	2004/04/16 13:19
-	0	wo/9747038	USPAT; US-PGPUB; EPO; JPO	2004/04/16 13:19